

### RF Power MOSFET Transistor 100W, 100-500 MHz, 28V

#### Features

- N-channel enhancement mode device
- DMOS structure
- Lower capacitances for broadband operation
- High saturated output power
- Lower noise figure than competitive devices
- RoHS Compliant

### ABSOLUTE MAXIMUM RATINGS AT 25° C

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V <sub>DS</sub>	65	V
Gate-Source Voltage	V <sub>GS</sub>	20	V
Drain-Source Current	I <sub>DS</sub>	12*	А
Power Dissipation	PD	250	W
Junction Temperature	TJ	200	°C
Storage Temperature	T <sub>STG</sub>	-55 to +150	°C
Thermal Resistance	$\theta_{\text{JC}}$	0.7	°C/W

### **TYPICAL DEVICE IMPEDANCES**

F (MHz)	Z <sub>IN</sub> (Ω)	Z <sub>LOAD</sub> (Ω)		
100	4.5-j6.0	14.5+j0.5		
300	2.25-j1.75	7.5j1.0		
500	1.5+j5.5	3.5+j3.5		
V <sub>DD</sub> =28V, I <sub>DQ</sub> =600 Ma, P <sub>OUT</sub> =100.0 W				

Z<sub>IN</sub> is the series equivalent input impedance of the device from gate to gate.

Z<sub>LOAD</sub> is the optimum series equivalent load impedance as measured from drain

### **ELECTRICAL CHARACTERISTICS AT 25°C**

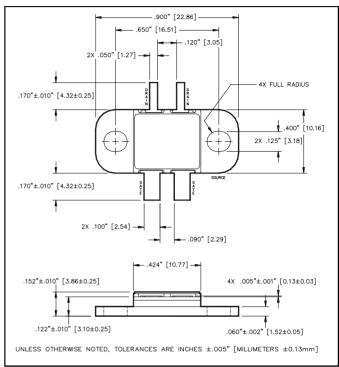
Parameter	Symbol	Min	Мах	Units	Test Conditions
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	65	-	V	V <sub>GS</sub> = 0.0 V , I <sub>DS</sub> = 15.0 mA
Drain-Source Leakage Current	I <sub>DSS</sub>	-	3.0	mA	$V_{GS} = 28.0 \text{ V}$ , $V_{GS} = 0.0 \text{ V}$
Gate-Source Leakage Current	I <sub>GSS</sub>	-	3.0	μA	$V_{GS} = 20.0 \text{ V}$ , $V_{DS} = 0.0 \text{ V}$
Gate Threshold Voltage	V <sub>GS(TH)</sub>	2.0	6.0	V	V <sub>DS</sub> = 10.0 V , I <sub>DS</sub> = 300.0 mA
Forward Transconductance	G <sub>M</sub>	1.5	-	S	$V_{\text{DS}}$ = 10.0 V , $I_{\text{DS}}$ 3000.0 mA , $~\Delta$ $V_{\text{GS}}$ = 1.0V, 80 $\mu s$ Pulse
Input Capacitance	C <sub>ISS</sub>	-	135	pF	V <sub>DS</sub> = 28.0 V , F = 1.0 MHz
Output Capacitance	C <sub>OSS</sub>	-	90	pF	V <sub>DS</sub> = 28.0 V , F = 1.0 MHz
Reverse Capacitance	C <sub>RSS</sub>	-	24	pF	V <sub>DS</sub> = 28.0 V , F = 1.0 MHz
Power Gain	G <sub>P</sub>	10	-	dB	$V_{DD}$ = 28.0 V, I <sub>DQ</sub> = 600.0 mA, P <sub>OUT</sub> = 100.0 W F =500 MHz
Drain Efficiency	ŋ₀	50	-	%	$V_{DD}$ = 28.0 V, $I_{DQ}$ = 600.0 mA, $P_{OUT}$ = 100.0 W F =500 MHz
Return Loss	RL	10	-	dB	V <sub>DD</sub> = 28.0 V, I <sub>DQ</sub> = 600.0 mA, P <sub>OUT</sub> = 100.0 W F =500 MHz
Load Mismatch Tolerance	VSWR-T	-	30:1	-	V <sub>DD</sub> = 28.0 V, I <sub>DQ</sub> = 600.0 mA, P <sub>OUT</sub> = 100.0 W F =500 MHz

\*Per side

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Rev. V1

#### PACKAGE OUTLINE



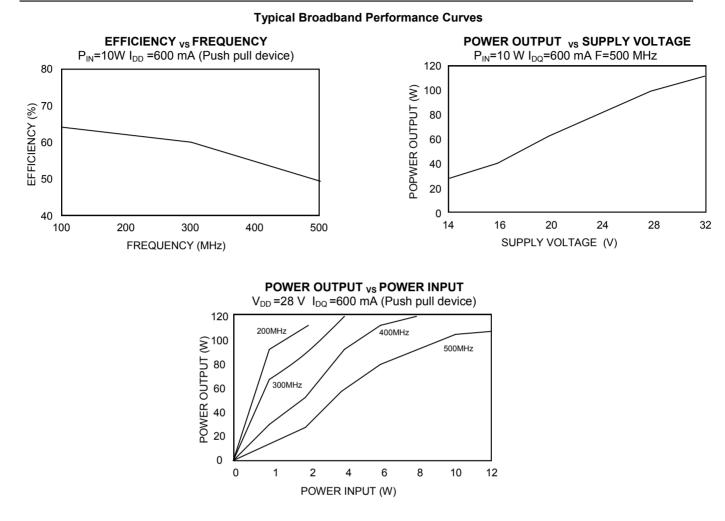
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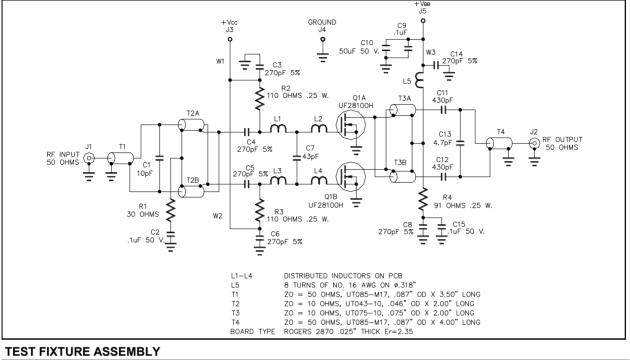


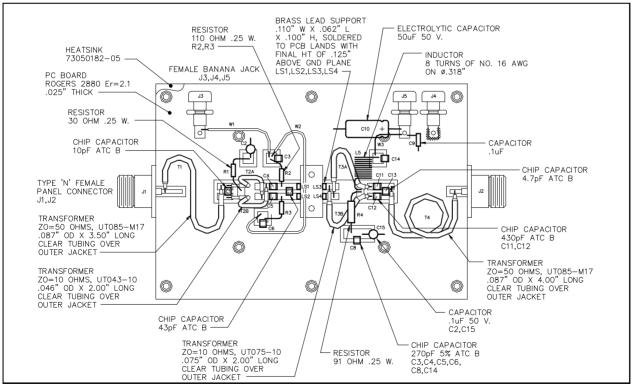
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# UF28100H

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### TEST FIXTURE SCHEMATIC





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